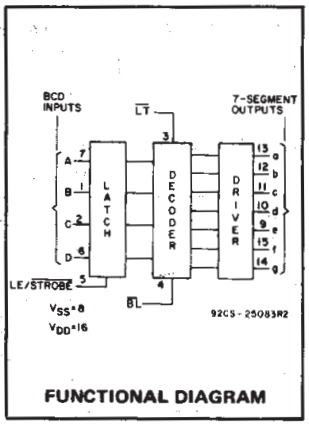
TEXAS INSTRUMENTS
Data sheet acquired from Harris Semiconductor
SCHS072

CD4511B Types

CMOS BCD-to-7-Segment Latch Decoder Drivers

High-Voltage Types (20-Volt Rating)



FUNCTIONAL DIAGRAM

■ CD4511B types are BCD-to-7-segment latch decoder drivers constructed with CMOS logic and n-p-n bipolar transistor output devices on a single monolithic structure. These devices combine the low quiescent power dissipation and high noise immunity features of RCA CMOS with n-p-n bipolar output transistors capable of sourcing up to 25 mA. This capability allows the CD4511B types to drive LED's and other displays directly.

Lamp Test ($\overline{LT}$), Blanking ($\overline{BL}$), and Latch Enable or Strobe inputs are provided to test the display, shut off or intensity-modulate it, and store or strobe a BCD code, respectively. Several different signals may be multiplexed and displayed when external multiplexing circuitry is used. The CD4511B is supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

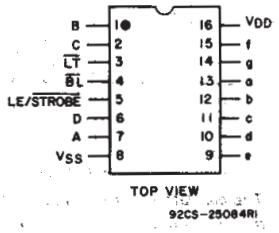
These devices are similar to the type MC14511.

Features:

- High-output-sourcing capability . . . . . up to 25 mA
- Input latches for BCD Code storage
- Lamp Test and Blanking capability
- 7-segment outputs blanked for BCD input codes > 1001
- 100% tested for quiescent current at 20 V
- Max. input current of 1 μA at 18 V, over full package-temperature range, 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings

Applications:

- Driving common-cathode LED displays
- Multiplexing with common-cathode LED displays
- Driving incandescent displays
- Driving low-voltage fluorescent displays



CD4511B
TERMINAL ASSIGNMENT

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
Voltages referenced to V_{SS} Terminal) . . . . . -0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS . . . . . -0.5V to V_{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT . . . . . ±10mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -55°C to +100°C 500mW
For T_A = +100°C to +125°C . . . . . Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) 100mW
OPERATING-TEMPERATURE RANGE (T_A) . . . . . -55°C to +125°C
STORAGE TEMPERATURE RANGE (T_{stg}) . . . . . -65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max . . . . . +265°C

OPERATING CONDITIONS AT T_A = 25°C Unless Otherwise Specified

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges

Characteristic	V_{DD}	Min.	Max.	Units
Supply-Voltage Range (T_A): (Full Package-Temperature Range)	–	3	18	V
Set-Up Time (t_S)	5	150	–	ns
	10	70	–	ns
	15	40	–	ns
Hold Time (t_H)	5	0	–	ns
	10	0	–	ns
	15	0	–	ns
Strobe Pulse Width (t_W)	5	400	–	ns
	10	160	–	ns
	15	100	–	ns

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	TEST CONDITIONS				LIMITS AT INDICATED TEMPERATURES (°C)							Units
	I_{OH} (mA)	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	+25 Min.	+25 Typ.	+25 Max.	
Quiescent Device Current: I_{DD} Max.	–	–	–	5	5	5	150	150	–	0.04	5	μA
	–	–	–	10	10	10	300	300	–	0.04	10	
	–	–	–	15	20	20	600	600	–	0.04	20	
	–	–	–	20	100	100	3000	3000	–	0.08	100	
Output Voltage: Low-Level V_{OL} Max.	–	–	0,5	5	0.05				–	0	0.05	V
	–	–	0,10	10	0.05				–	0	0.05	
	–	–	0,15	15	0.05				–	0	0.05	
High-Level V_{OH} Min.	–	–	0,5	5	4	4	4.2	4.2	4.1	4.55	–	V
	–	–	0,10	10	9	9	9.2	9.2	9.1	9.55	–	
	–	–	0,15	15	14	14	14.2	14.2	14.1	14.55	–	
Input Low Voltage, V_{IL} Max.	–	0.5,3.8		5	1.5				–	–	1.5	V
	–	1,8.8	–	10	3				–	–	3	
	–	1.5,13.8		15	4				–	–	4	
Input High Voltage, V_{IH} Min.	–	0.5,3.8		5	3.5				3.5	–	–	V
	–	1,8.8		10	7				7	–	–	
	–	1.5,13.8		15	11				11	–	–	
Output Drive Voltage: High Level V_{OH} Min.	0	–	–	5	4.0	4.0	4.20	4.20	4.10	4.55	–	V
	5	–	–		–	–	–	–	–	4.25	–	
	10	–	–		3.80	3.80	3.90	3.90	3.90	4.10	–	
	15	–	–		–	–	3.50	3.50	–	3.95	–	
	20	–	–		3.55	3.55	3.30	–	3.40	3.75	–	
	25	–	–		3.40	3.40	–	–	3.10	3.55	–	
	0	–	–	10	9.0	9.0	9.20	9.20	9.10	9.55	–	V
	5	–	–		–	–	–	–	–	9.25	–	
	10	–	–		8.85	8.85	9.00	9.00	9.00	9.15	–	
	15	–	–		–	–	–	–	–	9.05	–	
	20	–	–		8.70	8.70	8.40	8.40	8.60	8.90	–	
	25	–	–		8.60	8.60	–	–	8.30	8.75	–	
	0	–	–	15	14.0	14.0	14.20	14.20	14.10	14.55	–	V
	5	–	–		–	–	–	–	–	14.30	–	
	10	–	–		13.90	13.90	14.0	14.0	14.0	14.20	–	
	15	–	–		–	–	–	–	–	14.10	–	
	20	–	–		13.75	13.75	13.50	13.50	13.70	13.95	–	
	25	–	–		13.65	13.65	–	–	13.50	13.80	–	
Output Low (Sink) Current, I_{OL} Min.	–	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	–	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	–	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	–	
Input Current, I_{IN} Max.	–	0,18	0,18	18	±0.1	±0.1	±1	±1	–	$\pm 10^{-5}$	±0.1	μA

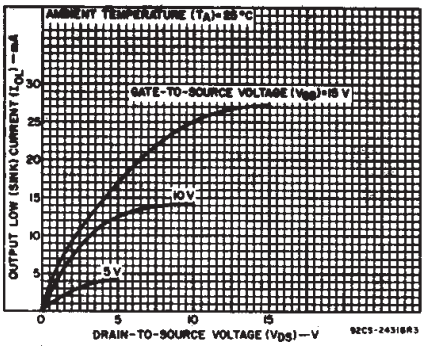


Fig. 1 – Typical output low (sink) current characteristics.

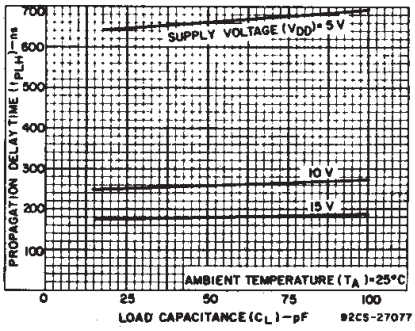


Fig. 2 – Typical data-to-output, low-to-high-level propagation delay time as a function of load capacitance.

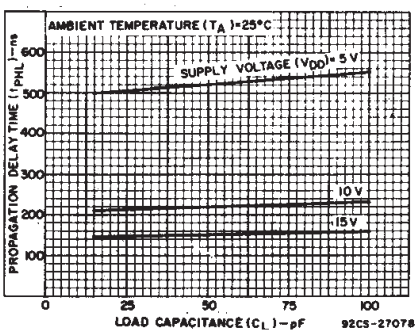


Fig. 3 – Typical data-to-output, high-to-low-level propagation delay time as a function of load capacitance.

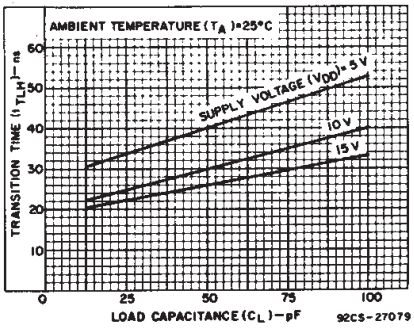


Fig. 4 – Typical low-to-high-level transition time as a function of load capacitance.

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C, Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 kΩ

CHARACTERISTIC	Test Conditions	LIMITS All Packages			UNITS
	V_{DD} Volts	Min.	Typ.	Max.	
Propagation Delay Time: (Data) High-to-Low Level, t_{PHL}	5	–	520	1040	ns
	10	–	210	420	
	15	–	150	300	
Low-to-High Level, t_{PLH}	5	–	660	1320	ns
	10	–	260	520	
	15	–	180	360	
Propagation Delay Time: ($\overline{BL}$) High-to-Low Level, t_{PHL}	5	–	350	700	ns
	10	–	175	350	
	15	–	125	250	
Low-to-High Level, t_{PLH}	5	–	400	800	ns
	10	–	175	350	
	15	–	150	300	
Propagation Delay Time: ($\overline{LT}$) High-to-Low Level, t_{PHL}	5	–	250	500	ns
	10	–	125	250	
	15	–	85	170	
Low-to-High Level, t_{PLH}	5	–	150	300	ns
	10	–	75	150	
	15	–	50	100	
Transition Time: Low-to-High Level, t_{TLH}	5	–	40	80	ns
	10	–	30	60	
	15	–	25	50	
High-to-Low Level, t_{THL}	5	–	125	310	ns
	10	–	75	185	
	15	–	65	160	
Minimum Set-Up Time, t_S	5	150	75	–	ns
	10	70	35	–	
	15	40	20	–	
Minimum Hold Time, t_H	5	0	−75	–	ns
	10	0	−35	–	
	15	0	−20	–	
Strobe Pulse Width, t_W	5	400	200	–	ns
	10	160	80	–	
	15	100	50		
Input Capacitance, C_{IN}		–	5	7.5	pF

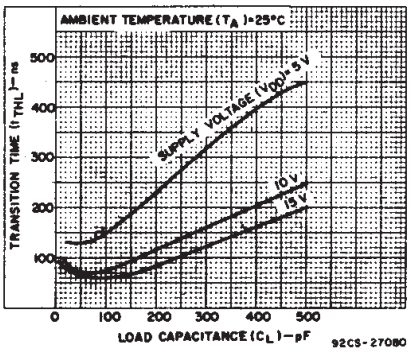


Fig. 5 – Typical high-to-low transition time as a function of load capacitance.

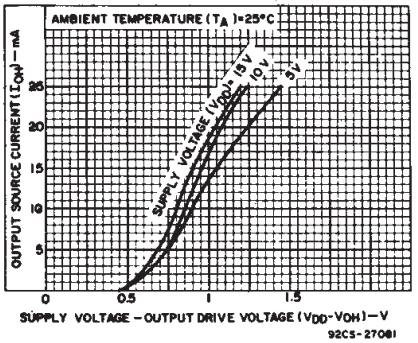


Fig. 6 – Typical voltage drop (V_{DD} to output) vs. output source current as a function of supply.

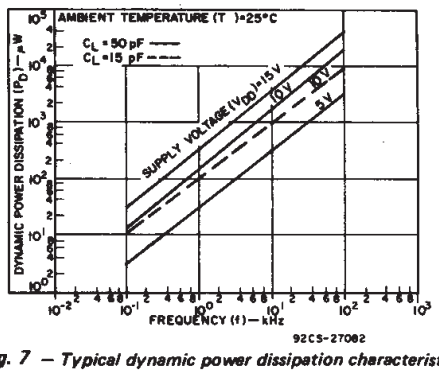


Fig. 7 – Typical dynamic power dissipation characteristics.

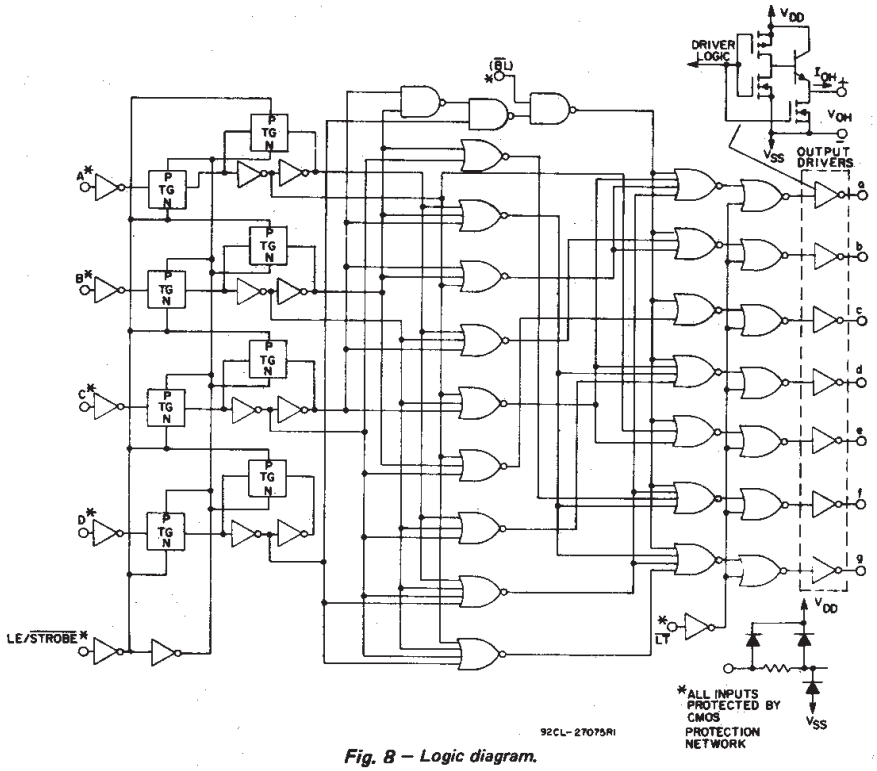


Fig. 8 – Logic diagram.

TRUTH TABLE

LE	$\overline{BI}$	$\overline{LT}$	D	C	B	A	a	b	c	d	e	f	g	Display
X	X	0	X	X	X	X	1	1	1	1	1	1	1	8
X	0	1	X	X	X	X	0	0	0	0	0	0	0	Blank
0	1	1	0	0	0	0	1	1	1	1	1	1	0	0
0	1	1	0	0	0	1	0	1	1	0	0	0	0	1
0	1	1	0	0	1	0	1	1	0	1	1	0	1	2
0	1	1	0	0	1	1	1	1	1	1	0	0	1	3
0	1	1	0	1	0	0	0	1	1	0	0	1	1	4
0	1	1	0	1	0	1	1	0	1	1	0	1	1	5
0	1	1	0	1	1	0	0	0	1	1	1	1	1	6
0	1	1	0	1	1	1	1	1	1	0	0	0	0	7
0	1	1	1	0	0	0	1	1	1	1	1	1	1	8
0	1	1	1	0	0	1	1	1	1	0	0	1	1	9
0	1	1	1	0	1	0	0	0	0	0	0	0	0	Blank
0	1	1	1	0	1	1	0	0	0	0	0	0	0	Blank
0	1	1	1	1	0	0	0	0	0	0	0	0	0	Blank
0	1	1	1	1	0	1	0	0	0	0	0	0	0	Blank
0	1	1	1	1	1	0	0	0	0	0	0	0	0	Blank
0	1	1	1	1	1	1	0	0	0	0	0	0	0	Blank
1	†	1	X	X	X	X	*							*

X ≡ Don't Care * Depends on BCD code previously applied when LE = 0

Note: Display is blank for all illegal input codes (BCD > 1001).

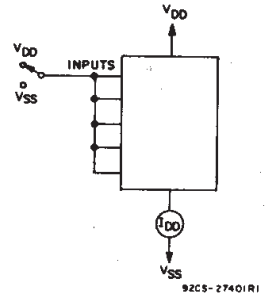


Fig. 9 – Quiescent device current.

TEST CIRCUITS

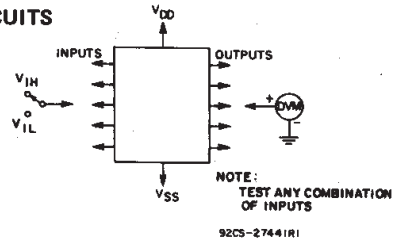
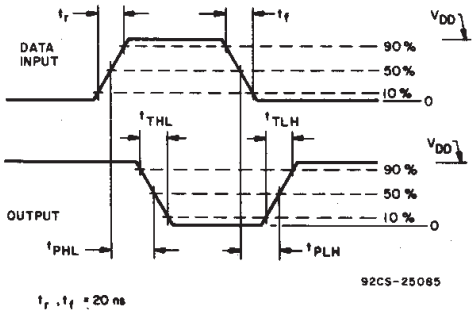


Fig. 10 – Input voltage.



t_r, t_f = 20 ns

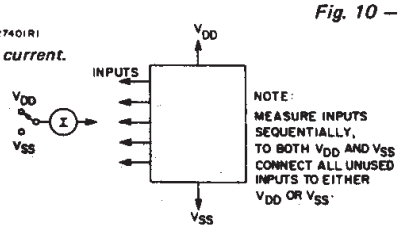


Fig.11 – Input current.

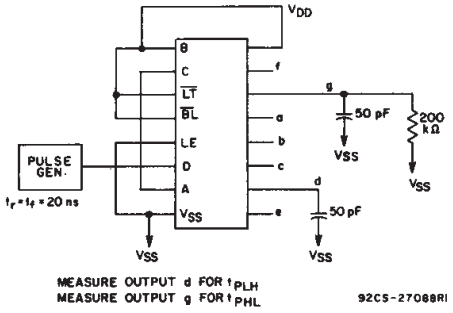


Fig.12 – Data propagation delay.

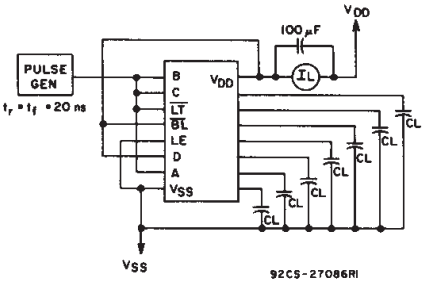
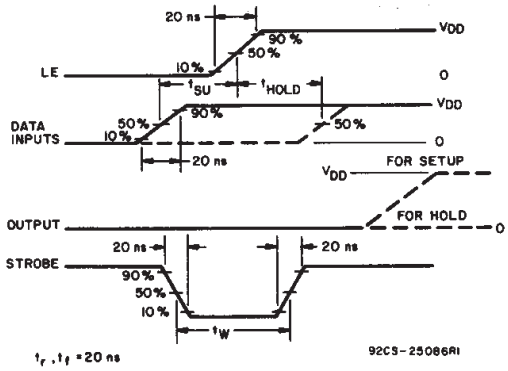


Fig. 13 – Dynamic power dissipation.

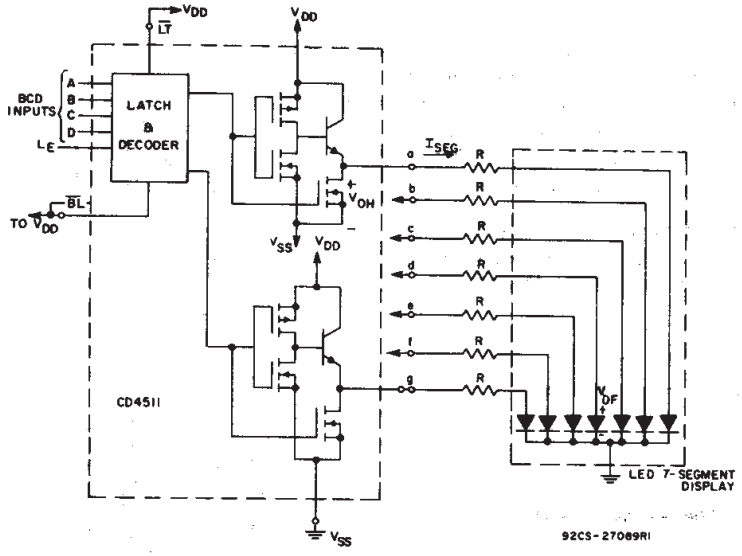


t_r, t_f = 20 ns

Fig. 14 – Dynamic waveforms.

APPLICATIONS

Interfacing with Various Displays

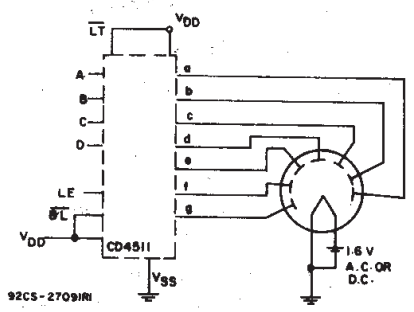


Duty Cycle = 100%

$I_{SEG} = I_{DIODE_{AVG.}}$ = 20 mA at Luminous Intensity/Segment = 250 microcandles

$$R = \frac{V_{OH} - V_{DF}}{I_{SEG}}$$

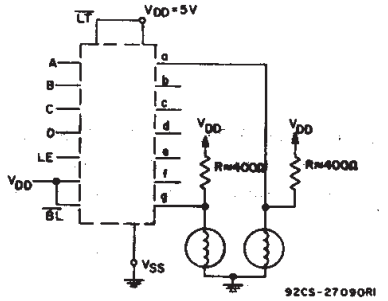
Fig. 15 - Driving common-cathode 7-segment LED displays (example Hewlet-Packard 5082-7740).



A medium-brightness intensity display can be obtained with low-voltage fluorescent displays such as the Tung-Sol Digivac S/G** Series.

**Trademark Tung-Sol Division Wagner Electric Co.

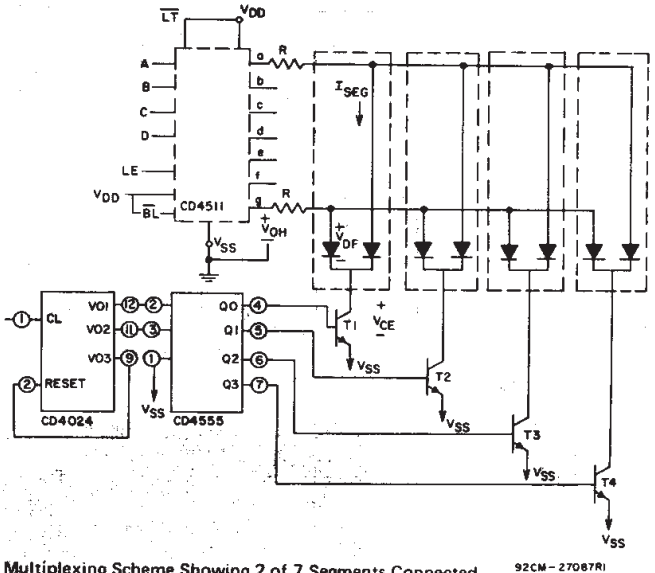
Fig. 16 – Driving low-voltage fluorescent displays.



2 of 7 Segments Shown Connected

Resistors R from V_{DD} to each 7-segment driver output are chosen to keep all Numitron segments slightly on and warm.

Fig. 17 – Driving incandescent displays (RCA Numitron DR2000 series displays).



Multiplexing Scheme Showing 2 of 7 Segments Connected

Transistors T_1–T_4 (RCA-2N3053 or 2N2102) have I_C Max. rating > 7xI_{SEG}

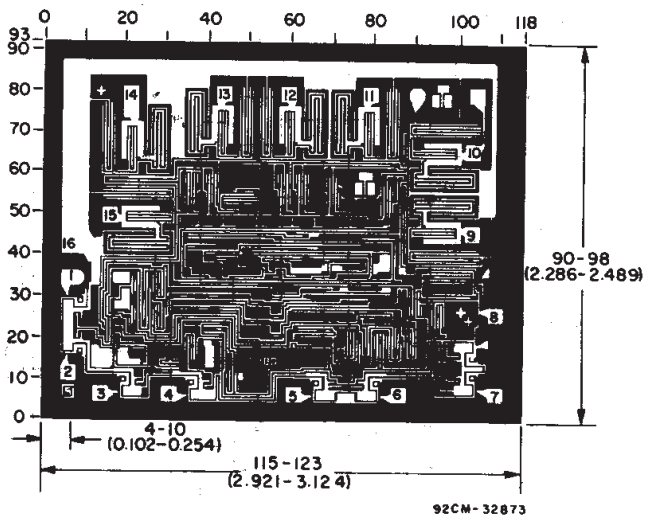
Duty Cycle = 25%

$I_{SEG} = (I_{DIODE_{AVG}}) \times 4$

$$R = \frac{(V_{OH} - V_{DF} - V_{CE})}{I_{SEG}}$$

All unused inputs on CD4555 are connected to V_{DD} or V_{SS}.

Fig. 18 – Multiplexing with common-cathode 7-segment LED displays (example Hewlet-Packard 5082-7404 4 character display or 4 discrete Monosanto Man 3 displays).



Dimensions and pad layout for CD4511B chip.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

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